PNP/NPN Epitaxial Planar Silicon Transistors



2SB1394/2SD2099

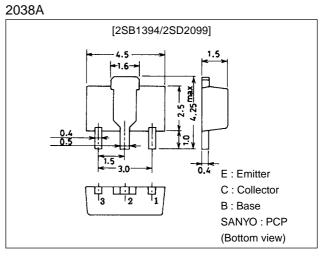
Compact Motor Driver Applications

Features

- \cdot Contains input resistance (R₁), base-to-emitter resistance (R_{BE}).
- \cdot Contains diode between collector and emitter.
- · Low saturation voltage.
- · Large current capacity.
- Small-sized package making it easy to provide highdensity, small-sized hybrid ICs.

Package Dimensions

unit:mm



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Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)40	V
Collector-to-Emitter Voltage	VCEO		(–)30	V
Emitter-to-Base Voltage	VEBO		()6	V
Collector Current	ι _C		()3	A
Collector Current (Pulse)	ICP		()5	A
Collector Dissipation	PC	Mounted on ceramic board (250mm ² ×0.8mm)	1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V _{CB} =(-)30V, I _E =0			(–)1.0	μΑ
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)0.5A	(–)70			
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)2A	(–)50			
Gain-Bandwidth Product	fT	V _{CE} =(-)2V, I _C =(-)0.5A		100		MHz
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(55)40		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)1A, I _B =(-)50mA		0.12	0.3	V
				(-0.18)	(-0.4)	V

Marking: 2SB1394: BN

2SD2099 : DL

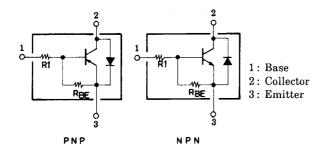
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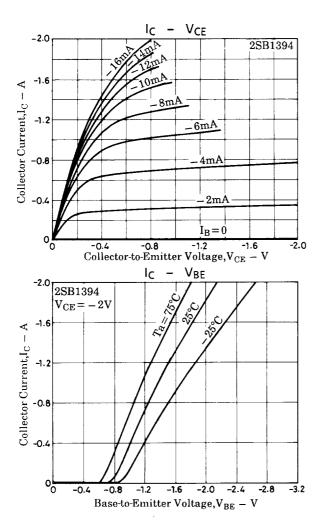
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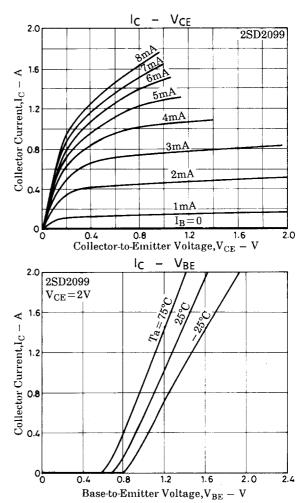
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Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	
Base-to-Emitter ON State Voltage	VBE(ON)	V _{CE} =(-)2V, I _C =(-)1A	(-)0.7	(–)1.5	(–)4.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10µA, I _E =0	(–)40			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO1	I _C =(−)10µA, R _{BE} =∞	(-)40			V
	V(BR)CEO2	I _C =(−)10mA, R _{BE} =∞	(–)30			V
Diode Forwad Voltage	VF	I _F =0.5A			(–)1.5	V
Base-to-Emitter Resistance	R _{BE}			0.8		kΩ
Base Resistance	R ₁		60	90	120	Ω

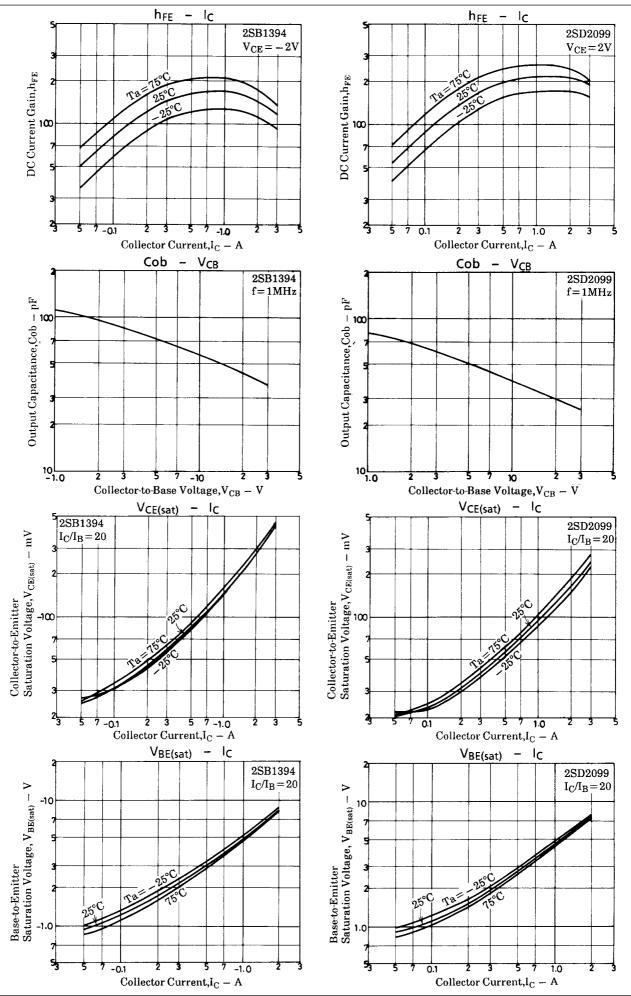
Electrical Connection

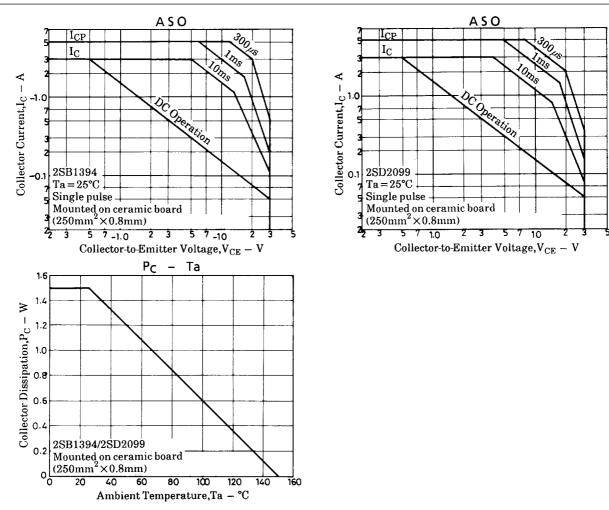






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